Surface Mount Transient Voltage Suppressor Diode

Features

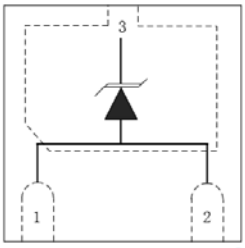
- ✧ Surge protection of one power line
- ✧ Solid-state silicon-avalanche technology
- ✧ Working Voltage: 24.0V
- ✧ Peak Power up to 5670 Watts @ 8 x 20μs Pulse
- ✧ Low Leakage current
- ✧ Low clamping voltage
- ✧ IEC 61000-4-2 (ESD) ±30kV (air), ±30kV (contact)

Applications

- ✧ Cellular Handsets & Accessories
- ✧ Portable devices
- ✧ Power line

Mechanical Data

- ✧ UL Flame Rating : UL94V-0
- ✧ Reel Size : 7 inch
- ✧ RoHS/WEEE Compliant



Circuit Diagram



DFN2020-3L

Absolute Maximum Rating at T_A = 25 °C, unless otherwise specified

Rating	Symbol	Value	Units
Peak Pulse Power (t_p =8/20μs)	P_{PP}	5670	Watts
Peak Pulse Current (t_p =8/20μs)	I_{pp}	135	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	±30 ±30	kV
Lead Soldering Temperature	T_L	260(10seconds)	℃
Junction Temperature	T_J	-55 to + 125	℃
Storage Temperature	T_{stg}	-55 to + 150	℃

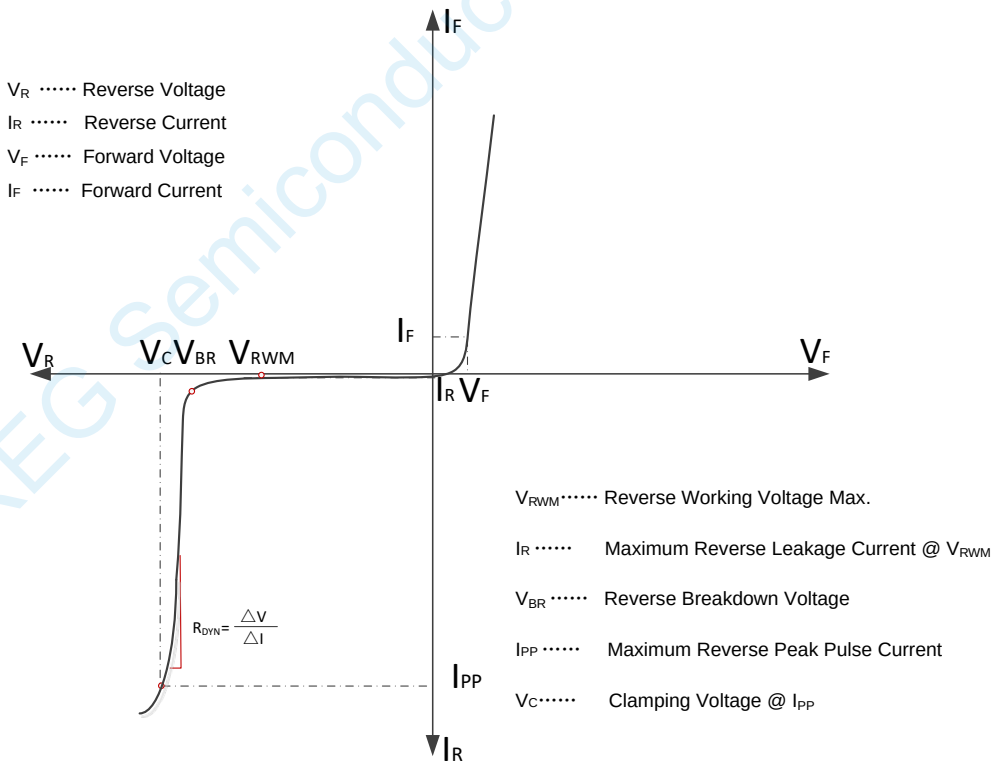
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Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typical	Max.	Units
Reverse Stand-Off Voltage	V_{RWM}				24.0	V
Reverse Breakdown Voltage	V_{BR}	I_T=1mA	26			V
Reverse Leakage Current	I_R	V_{RWM}=24.0V, T=25℃			1	μA
Peak Pulse Current	I_{PP}	tp =8/20μs			135	A
Clamping Voltage	V_C	I_{PP}=100A, tp=8/20μs （pin3 to pin1 and pin2）		36	38	V
Clamping Voltage	V_C	I_{PP}=135A, tp=8/20μs （pin3 to pin1 and pin2）		39	42	V
Junction Capacitance	C_J	V_R = 0V, f = 1MHz		800	1000	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
1. All parameters specified at T_A = 25°C unless otherwise noted.
2. These parameters are guaranteed by design and characterization.
3. Standard IEC 61000−4−2 with $C_{Discharge}$ = 150 pF, $R_{Discharge}$ = 330 Ω

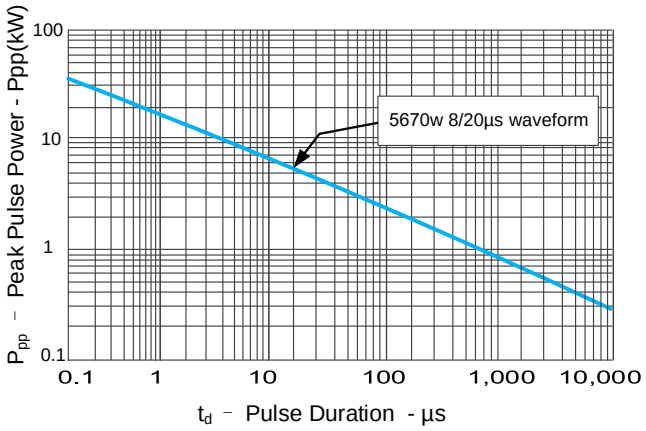
Electrical Parameters at T_A = 25 °C, unless otherwise specified



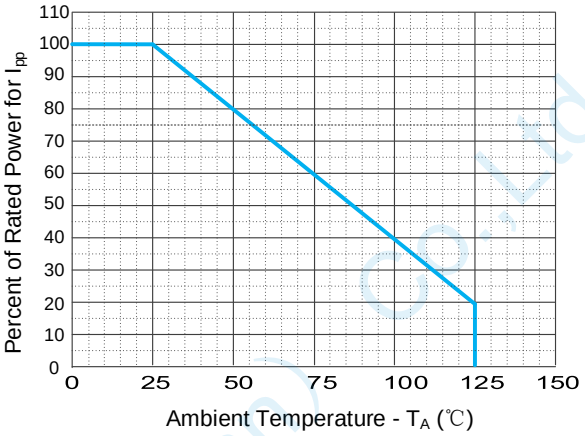
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Typical Characteristics at T_A = 25 °C, unless otherwise specified

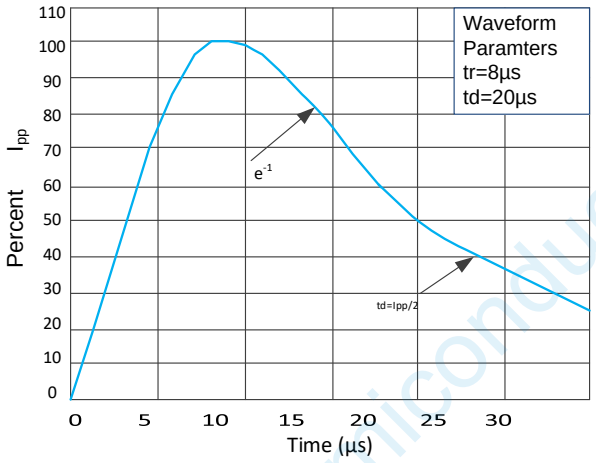
Non-repetitive Peak Pulse Power vs. Pulse Time



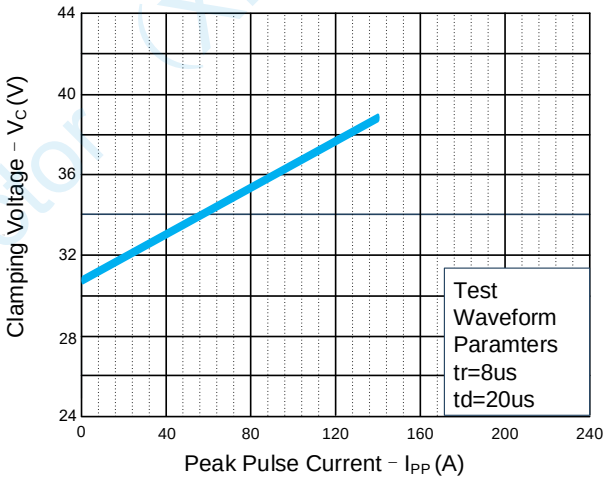
Power derating vs. Ambient temperature



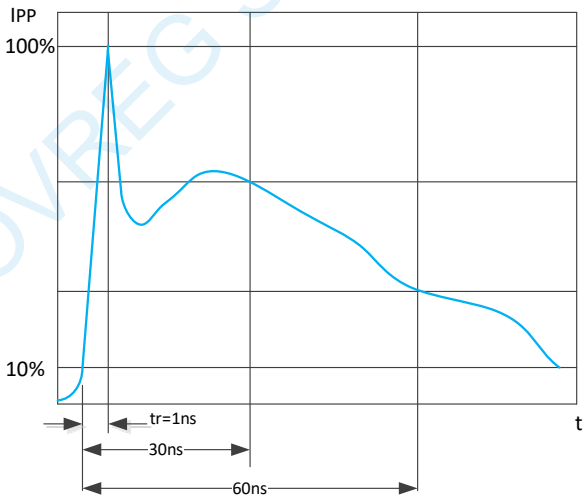
8/20uS Pulse Waveform



Reverse Clamping Voltage vs. Peak Pulse Current

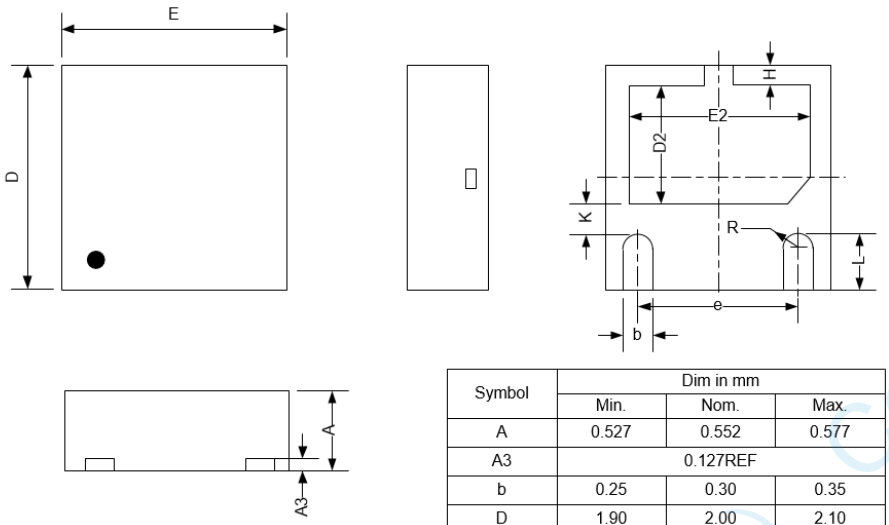


IEC61000-4-2 +8kV Pulse Waveform



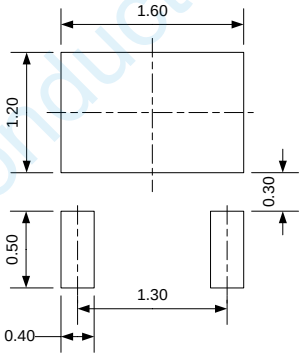
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Package Information



Symbol	Dim in mm		
	Min.	Nom.	Max.
A	0.527	0.552	0.577
A3		0.127REF	
b	0.25	0.30	0.35
D	1.90	2.00	2.10
E	1.90	2.00	2.10
D2	0.95	1.05	1.15
E2	1.40	1.50	1.60
e	1.20	1.30	1.40
H	0.20	0.25	0.30
K	0.20	0.30	0.40
L	0.35	0.40	0.45
R	0.13	-	-

Recommend PCB Layout



Notes: This PCB Layout Is For Reference Purposes Only

Ordering Information



Ordering Information

Part number	Material	Type	Reel size	MOQ	MOQ/internal box	MOQ/carton
OVE88E15M1M	GREEN	T/R	7 inch	3k/reel	10reel= 30k/box	4boxes=120k/carton

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